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CCS H83

SJ

INDUSTRY STANDARD OF THE PEOPLE'S REPUBLIC OF CHINA

SJ 21477-2018

Technical requirements for InP poly crystal synthesis process

磷化铟多晶材料合成工艺技术要求

(English Translation)

Issued by: Ministry of Industry and Information Technology

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1 Foreword

SJ 21477-2018 was issued by Ministry of Industry and Information Technology on 29 December 2018.

The SJ prefix, without a suffix, marks a mandatory standard: within its scope, compliance is required.

The document runs to 8 pages in English translation.

2 Scope Preview

SJ 21477-2018 is filed under Chinese Standard Classification H83, in the field of metallurgy.

This catalogue holds 1,191 other SJ standards without an ICS number.

In this catalogue, SJ standards carry edition years from 1965 to 2021.

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3 About this standard

Sector: Electronics Industry Standard

Issued by: Ministry of Industry and Information Technology

English translation: about 8 pages (approximate)

Chinese original: about 11,114 characters

4 Related standards

Standards on related subjects:

GB/T 25074-2017 - Solar-grade polycrystalline silicon

SJ/T 11488-2015 - Test method for measuring resistivity, hall coefficient and determining hall mobility in semi-insulating GaAs single crystals

YS/T 13-2015 - High pure germanium tetrachloride

SJ 21478-2018 - Indium phosphide single crystal growth process technical requirements

SJ 21476-2018 - Technical requirements for annealing of InP single crystal

SJ 21475-2018 - Indium phosphide single wafer geometric parameter test method

5 Classification and status

Chinese Standard Classification (CCS): H 83

Prefix SJ: mandatory standard.

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